

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
		(transistor liquid adj crystal adj display) with (glass near3 substrate)) with (driving adj voltage electric adj field)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/01 15:14
		("(microadjstructuremicrostructure)with(gripermanipulator)").PN.	US-PGPU B; USPAT; USOCR	OR	OFF	2004/11/30 13:36
L9	19	"31" and (field with strenght)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/02 06:05
L10	11565	(transistor liquid adj crystal adj display) with (glass near3 substrate)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/02 06:06
L11	3397	L10 and ((transistor liquid adj crystal adj display) with (voltage))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/02 06:06
L12	1818	L11 and ((transistor liquid adj crystal adj display) with (drain))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/02 06:06
L13	398	L12 and (drain with (concentration density atomic))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/02 06:06
L14	231	L13 and (voltage with (lower higher different))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/02 06:06
L15	123	L14 and (voltage near2 driv\$3)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/02 06:06
L16	0	L15 and (field with strenght)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/02 06:07
L17	1	(field with strenght) with transistor	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/02 06:07
L18	27	field near4 strenght	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/02 06:20
L19	0	field near4 strenght with gate	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/02 06:20

S17	1374	("tft" thin adj film adj transistor) with (driving near3 voltage)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/01 14:02
S18	220	("tft" thin adj film adj transistor) with (driving near3 voltage) with drain	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/01 13:30
S19	74	S18 and (drain with concentration)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/01 14:01
S20	0	S19 and electric adj field	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/01 14:01
S21	45	S19 and electric adj field	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/01 14:01
S22	5461	("tft" thin adj film adj transistor thin adj film) with ((driving near3 voltage) with field electric adj field)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/01 14:03
S23	338	transistor with ((driving near3 voltage) with (field electric adj field))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/01 14:04
S24	22	S23 and (drain with concentration)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/01 14:14
S25	8	(transistor with (glass near3 substrate)) with driving adj voltage	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/01 14:58
S26	34	(transistor with (glass near3 substrate)) with electric adj field	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/01 14:18
S27	39	(transistor with (glass near3 substrate)) with (driving adj voltage electric adj field)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/01 15:14
S28	136	(transistor liquid adj crystal adj display) with (glass near3 substrate) with (driving adj voltage electric adj field)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/01 15:15
S29	136	S28 and (transistor liquid adj crystal adj display glass near3 substrate driving adj voltage electric adj field)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/01 15:16

S30	147	(transistor liquid adj crystal adj display) with (glass near3 substrate) with (driving near4 voltage electric adj field)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/01 15:34
S31	147	S30 and (transistor liquid adj crystal adj display glass near3 substrate driving near4 voltage electric adj field)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/01 15:17
S32	24	S31 and (drain with concentration)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/01 15:17
S33	11565	(transistor liquid adj crystal adj display) with (glass near3 substrate)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/01 15:35
S34	3397	S33 and ((transistor liquid adj crystal adj display) with (voltage))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/01 15:36
S35	1818	S34 and ((transistor liquid adj crystal adj display) with (drain))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/01 15:37
S36	398	S35 and (drain with (concentration density atomic))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/01 15:46
S37	830	S35 and (voltage with (lower higher))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/01 15:43
S38	620	S37 and (voltage with driv\$3)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/01 15:41
S39	573	S37 and (voltage near6 driv\$3)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/01 15:41
S40	543	S37 and (voltage near3 driv\$3)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/01 15:44
S41	231	S36 and (voltage with (lower higher different))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/01 15:44
S42	129	S41 and (voltage near3 driv\$3)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/01 15:45

S43	123	S41 and (voltage near2 driv\$3)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/01 15:45
S44	103	S43 and (drain with concentration)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/02 06:06
S45	34	d446525	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/01 16:02
S46	60	S43 and (drain near5 concentration)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/01 17:39
S47	115	nanowir\$3.ti.	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/01 17:09
S48	45	S46 and electric adj field	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/02 06:05